

RAMAKRISHNA MISSION VIDYAMANDIRA

(Residential Autonomous College affiliated to University of Calcutta)

B.A./B.Sc. THIRD SEMESTER EXAMINATION, DECEMBER 2016

SECOND YEAR [BATCH 2015-18]

ELECTRONICS [General]

Paper : III

Date : 16/12/2016

Time : 11 am – 1 pm

Full Marks : 50

Answer any five questions:

[5×10]

1. a) Define accuracy, precision, resolution and sensitivity.
b) Write the working principle of a CRT with the help of Schematic Diagram. [4+6]
2. a) Compare TTL, ECL and CMOS logic families.
b) Realize 2-input NAND logic gates using TTL and CMOS logic respectively.
c) Draw and explain the schematic of a CMOS Device. [3+3+4]
3. a) State and explain Moore's Law.
b) Compare MSI, LSI and VLSI.
c) Design a FULL-ADDER circuit using Verilog code. [3+3+4]
4. a) Draw a basic block diagram of a CRO.
b) Explain how frequency and phase angle can be measured by a CRO using lissajous figures. [5+5]
5. a) Explain the method of measuring displacement using LVDT.
b) State advantages of LVDT.
c) An ac LVDT has the following data. Input = 6.3 V, output = 5.2 V, range ± 0.5 in. Determine
(i) The output voltage vs core position for a core movement going from + 0.45 in to – 0.30 in.
(ii) The output voltage when the core is at – 0.25 in from the centre. [5+2+3]
6. A strain gauge having a resistance of $350\ \Omega$ and a gauge factor of 2.1 is cemented to a structure subjected to a stress of $150 \times 10^6\ N/m^2$. The modulus of elasticity is $200 \times 10^9\ N/m^2$. Find the change in resistance. Derive the equation also. [10]
7. Write short notes on any two of the following: [2 x 5]
 - a) Design Domains of VLSI
 - b) FPGA
 - c) VLSI chips
 - d) Transducers and its property